



## Monolayer hBN

hBN Coverage: 100% with sporadic adlayers (see optical image above)

Bandgap: 5.97 eV

Grain size: >4 μm

Raman Peak: 1370 /cm-1

## Substrate

Our 4-inch (100mm) Si/SiO<sub>2</sub> wafers are sourced from a reliable, quality-assured supplier.

Type/Doping: P/B

Wafer Thickness : 500 +/- 50μm

Oxide Thickness: 300nm

Resistivity: 1 – 10 (ohm-cm)

Orientation: <1-0-0>

Metal Impurities: 1.00e10 – 5.00e10 (at/cm<sup>2</sup>)